AMENDMENTS TO THE CLAIMS

Please amend the claims as follows.

1. (Currently amended) A method for manufacturing a nitride semiconductor chip, said method comprising the steps of:

growing nitride crystals of a hexagonal system on a surface of a substrate;

cutting said substrate along two directions that form a 120 degree angle;

forming a light-emitting section on a central section of the nitride semiconductor chip; and

forming ~~an~~ triangular electrodes at opposing ends of ~~a planar surface of~~ the nitride semiconductor chip.

2. (Previously presented) A method according to claim 1, further comprising, between said growing step and said cutting step, the step of grinding a back surface of said substrate.

3. (Previously presented) A method according to claim 2, further comprising the step of:

making scratches on one of a front surface and a back surface of said substrate, between said grinding step and said cutting step, wherein

said cutting step is performed by cutting said substrate along directions of said scratches.

4. (Previously presented) A method according to claim 1, wherein said semiconductor chip has a planar shape of a rhombus.

5. (Original) A method according to claim 1, wherein said substrate is sapphire.

6. (Original) A method according to claim 1, wherein said nitride crystals include GaN.

7. (Withdrawn) A nitride semiconductor chip, comprising:

a substrate; and

nitride crystals of a hexagonal system and formed on said substrate; wherein

the planer shape of said semiconductor chip is a rhombus having an interior angle of 120 degrees.

8. (Withdrawn) A semiconductor chip according to claim 7, further comprising:

a light emitting section formed on the central section of said rhombus of the planer shape of said semiconductor chip; and

electrode sections formed at both ends of said rhombus to pinch said light emitting section.

9. (Withdrawn) A semiconductor chip according to claim 8, wherein the planer shape of said electrode sections is triangular.

10. (Withdrawn) A semiconductor chip according to claim 7, wherein said substrate is a sapphire.

11. (Withdrawn) A semiconductor chip according to claim 7, wherein said nitride crystals include a GaN.

12. (Currently amended) A method for manufacturing a nitride semiconductor chip, said method comprising the steps of:

growing nitride crystals of a hexagonal system on a surface of a substrate;

grinding a back surface of said substrate; ~~and~~

cutting said substrate along two directions that form a 120 degree angle; and

forming triangular electrodes at opposing ends of the semiconductor chip.

13. (Previously presented) A method according to claim 12, further comprising the step of:

making scratches on one of a front and a back surface of said substrate, between said grinding step and said cutting step, wherein

said cutting step is performed by cutting said substrate along directions of said scratches.

14. (Previously presented) A method according to claim 12, wherein said semiconductor chip has a planar shape of a rhombus.

15. (Previously presented) A method according to claim 12, wherein said substrate is sapphire.

16. (Previously presented) A method according to claim 12, wherein said nitride crystals include GaN.